**Dual 2-input OR gate** 

Rev. 1 — 12 March 2014

**Product data sheet** 

### 1. General description

The 74AHC2G32-Q100; 74AHCT2G32-Q100 are high-speed Si-gate CMOS devices. They provide two 2-input OR gates.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
   Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)

## 3. Ordering information

#### Table 1.Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AHC2G32DP-Q100	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads;	SOT505-2					
74AHCT2G32DP-Q100			body width 3 mm; lead length 0.5 mm						
74AHC2G32DC-Q100	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package;	SOT765-1					
74AHCT2G32DC-Q100			8 leads; body width 2.3 mm						



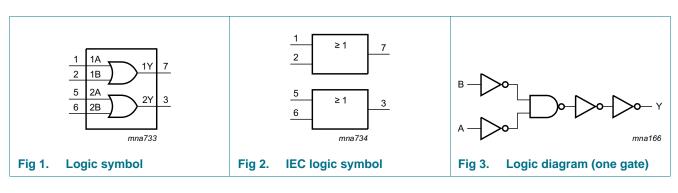
**Dual 2-input OR gate** 

### 4. Marking

Table 2. Marking	
Type number	Marking code <sup>[1]</sup>
74AHC2G32DP-Q100	A32
74AHCT2G32DP-Q100	C32
74AHC2G32DC-Q100	A32
74AHCT2G32DC-Q100	C32

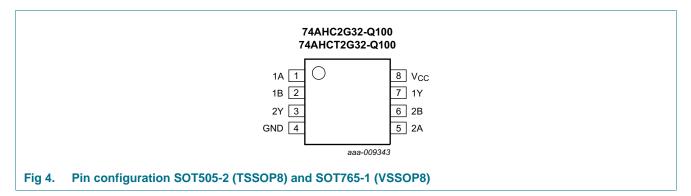
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram



### 6. Pinning information

#### 6.1 Pinning



Dual 2-input OR gate

### 6.2 Pin description

Table 3.   Pin description		
Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V <sub>CC</sub>	8	supply voltage

## 7. Functional description

#### Table 4.Function table<sup>[1]</sup>

Input		Output
nA	nB	nY
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

[1] H = HIGH voltage level; L = LOW voltage level.

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+7.0	V
VI	input voltage			-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V	[1]	-20	-	mA
I <sub>OK</sub>	output clamping current	$V_{O}$ < -0.5 V or $V_{O}$ > $V_{CC}$ + 0.5 V	[1]	-	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$		-	±25	mA
I <sub>CC</sub>	supply current			-	75	mA
I <sub>GND</sub>	ground current			-75	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[2]	-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.

Dual 2-input OR gate

## 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74Ał	IC2G32-	Q100	74AH	-Q100	Unit	
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	t/∆V input transition rise	$V_{CC}$ = 3.3 V $\pm$ 0.3 V	-	-	100	-	-	-	ns/V
and	and fall rate	$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	-	-	20	-	-	20	ns/V

## **10. Static characteristics**

#### Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C	to +85 °C	_40 °C	Unit	
			Min	Тур	Max	Min	Max	Min	Мах	
74AHC2	G32-Q100			-1						-1
V <sub>IH</sub>	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V <sub>CC</sub> = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V <sub>CC</sub> = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = -50 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_0 = -50 \ \mu\text{A}; \ V_{CC} = 3.0 \ \text{V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_0 = -50 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = 50 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_0 = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
l <sub>l</sub>	input leakage current	$V_I = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA
I <sub>CC</sub>	supply current		-	-	1.0	-	10	-	40	μA
CI	input capacitance		-	1.5	10	-	10	-	10	pF

**Dual 2-input OR gate** 

Symbol	Parameter	Conditions		25 °C		_40 °C	to +85 °C	–40 °C to +125 °C		Unit
			Min	Тур	Мах	Min	Max	Min	Max	1
74AHCT	2G32-Q100									
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
l <sub>l</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ
I <sub>CC</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	1.0	-	10	-	40	μΑ
∆l <sub>CC</sub>	additional supply current	per input pin; V <sub>I</sub> = 3.4 V; other inputs at V <sub>CC</sub> or GND; $I_O = 0 A$ ; V <sub>CC</sub> = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
CI	input capacitance		-	1.5	10	-	10	-	10	pF

## Table 7.Static characteristics ...continuedVoltages are referenced to GND (ground = 0 V).

## **11. Dynamic characteristics**

### Table 8. Dynamic characteristics

#### GND = 0 V; for test circuit see <u>Figure 6</u>.

Symbol	Parameter	Conditions		25 °C		–40 °C	to +85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC2	G32-Q100									
t <sub>pd</sub> propagation	propagation	nA, nB to nY; see Figure 5								
	delay	V <sub>CC</sub> = 3.0 V to 3.6 V [2]								
		C <sub>L</sub> = 15 pF	-	4.4	7.9	1.0	9.5	1.0	10.0	ns
		C <sub>L</sub> = 50 pF	-	6.3	11.4	1.0	13.0	1.0	14.5	ns
		$V_{\rm CC} = 4.5 \text{ V to } 5.5 \text{ V}$ [3]								
		C <sub>L</sub> = 15 pF	-	3.2	5.5	1.0	6.5	1.0	7.0	ns
		C <sub>L</sub> = 50 pF	-	4.6	7.5	1.0	8.5	1.0	9.5	ns
C <sub>PD</sub>	power dissipation capacitance	$\label{eq:constraint} \begin{array}{ll} \text{per buffer;} & [4] \\ C_L = 50 \text{ pF; } f_i = 1 \text{ MHz;} \\ V_I = \text{GND to } V_{\text{CC}} \end{array}$	-	16	-	-	-	-	-	pF

**Dual 2-input OR gate** 

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
74AHCT	2G32-Q100										
t <sub>pd</sub> propagation	nA, nB to nY; see Figure 5	[1]									
	delay	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	[3]								
		C <sub>L</sub> = 15 pF		-	3.3	6.9	1.0	8.0	1.0	9.0	ns
		C <sub>L</sub> = 50 pF		-	4.8	7.9	1.0	9.0	1.0	10.0	ns
C <sub>PD</sub>	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	17	-	-	-	-	-	pF

## **Table 8. Dynamic characteristics** ... continued GND = 0 V: for test circuit see Figure 6.

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2] Typical values are measured at V<sub>CC</sub> = 3.3 V.

[3] Typical values are measured at  $V_{CC}$  = 5.0 V.

[4]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i = input frequency in MHz;$ 

 $f_o$  = output frequency in MHz;

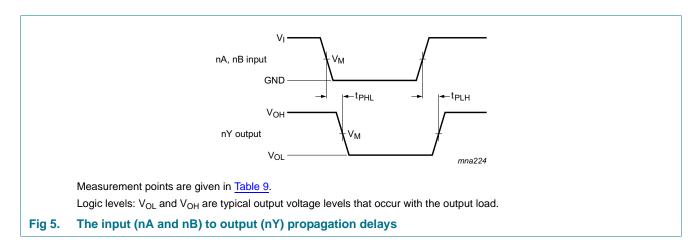
 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of the outputs.

## 12. Waveforms and test circuit



#### Table 9. Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74AHC2G32-Q100	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
74AHCT2G32-Q100	1.5 V	0.5V <sub>CC</sub>

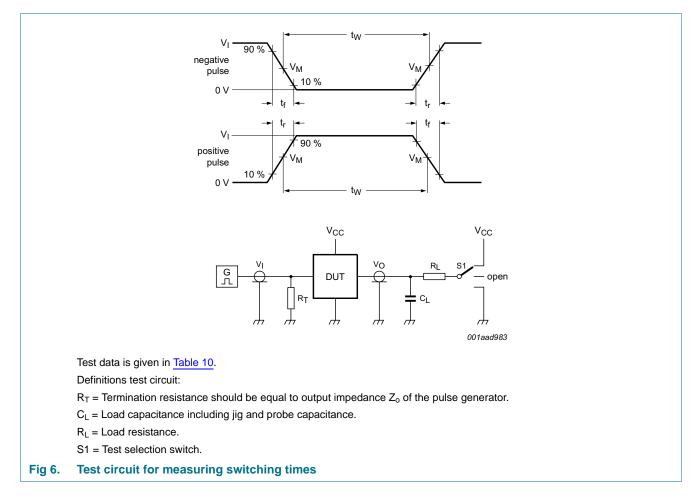
74AHC\_AHCT2G32\_Q100
Product data sheet

6 of 13

### **NXP Semiconductors**

## 74AHC2G32-Q100; 74AHCT2G32-Q100

#### Dual 2-input OR gate

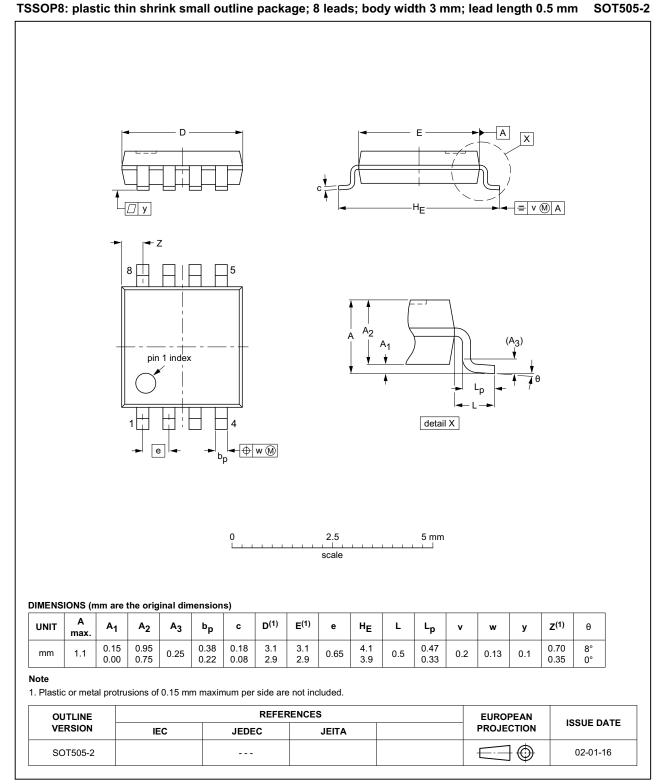


#### Table 10. Test data

Туре	Input		Load		S1 position			
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PHL</sub> , t <sub>PLH</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
74AHC2G32-Q100	V <sub>CC</sub>	≤ 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>	
74AHCT2G32-Q100	3 V	≤ 3 ns	15 pF, 50 pF	1 kΩ	open	GND	V <sub>CC</sub>	

**Dual 2-input OR gate** 

### 13. Package outline



#### Fig 7. Package outline SOT505-2 (TSSOP8)

All information provided in this document is subject to legal disclaimers.

**Dual 2-input OR gate** 

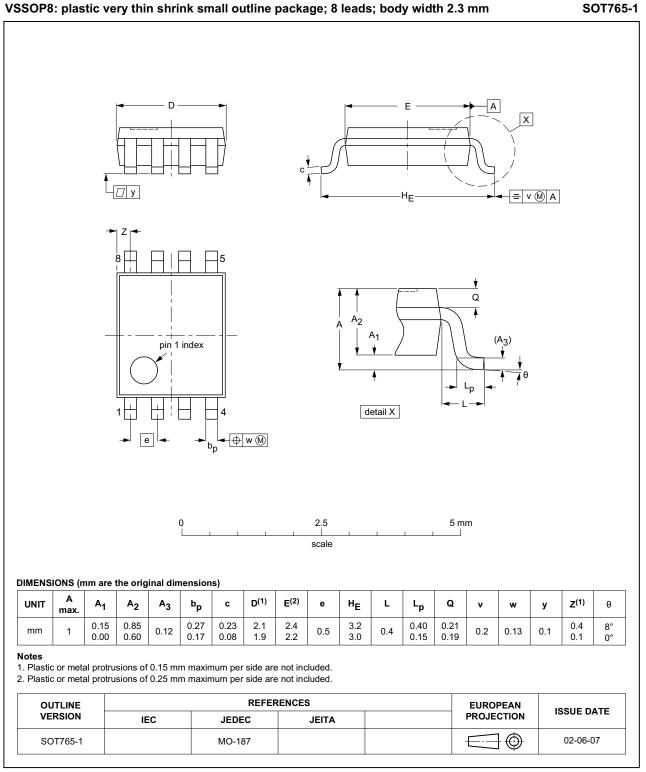


Fig 8. Package outline SOT765-1 (VSSOP8)

**Dual 2-input OR gate** 

## 14. Abbreviations

Table 11. Abbreviations		
Acronym	Description	
CDM	Charged Device Model	
CMOS	Complementary Metal-Oxide Semiconductor	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
НВМ	Human Body Model	
MIL	Military	
MM	Machine Model	
TTL	Transistor-Transistor Logic	

## 15. Revision history

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G32_Q100 v.1	20140312	Product data sheet	-	-

## 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

#### 16.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### 16.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

#### Suitability for use in automotive applications - This NXP

Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

#### **Dual 2-input OR gate**

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

**Translations** — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

#### 16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## **17. Contact information**

For more information, please visit: <u>http://www.nxp.com</u>

For sales office addresses, please send an email to: salesaddresses@nxp.com

12 of 13

Dual 2-input OR gate

### **18. Contents**

1	General description 1
2	Features and benefits 1
3	Ordering information 1
4	Marking 2
5	Functional diagram 2
6	Pinning information 2
6.1	Pinning 2
6.2	Pin description 3
7	Functional description 3
8	Limiting values
9	Recommended operating conditions 4
10	Static characteristics 4
11	Dynamic characteristics 5
12	Waveforms and test circuit
13	Package outline 8
14	Abbreviations 10
15	Revision history 10
16	Legal information 11
16.1	Data sheet status 11
16.2	Definitions 11
16.3	Disclaimers 11
16.4	Trademarks 12
17	Contact information 12
18	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP Semiconductors N.V. 2014.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 12 March 2014 Document identifier: 74AHC\_AHCT2G32\_Q100